

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	372	438/619.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/08 08:49
S1	1	((via or vias) and ((sacrificial near5 (etch or etching)) with (air near2 (gap or core or void or slot or space or pocket)))) and (fluoride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/08 08:49
S2	40	(via or vias) and ((sacrificial near5 (etch or etching)) with (air near2 (gap or core or void or slot or space or pocket)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 15:43
S3	1	("6413852").PN.	USPAT; USOCR	OR	OFF	2004/08/12 14:25
S4	12	"6413852"	US-PGPUB; USPAT	OR	OFF	2004/08/12 14:25
S5	5	US-5668398-\$.DID. OR US-5918149-\$.DID. OR US-5963830-\$.DID. OR US-6120844-\$.DID. OR US-6204200-\$.DID.	USPAT	OR	OFF	2004/08/12 15:48
S6	0	(US-5668398-\$.DID. OR US-5918149-\$.DID. OR US-5963830-\$.DID. OR US-6120844-\$.DID. OR US-6204200-\$.DID.) and xexon	USPAT	OR	OFF	2004/08/12 15:49
S7	0	(US-5668398-\$.DID. OR US-5918149-\$.DID. OR US-5963830-\$.DID. OR US-6120844-\$.DID. OR US-6204200-\$.DID.) and xenon	USPAT	OR	OFF	2004/08/12 15:49
S8	108281	((xenon near3 difluoride) near3 etch or etching or etchant) and (semiconductor or chip or die or ic)	USPAT	OR	OFF	2004/08/12 15:50
S9	1958	((xenon near3 difluoride) near3 etch or etching or etchant) near5 sacrificial) and (semiconductor or chip or die or ic)	USPAT	OR	OFF	2004/08/12 15:54
S10	1958	((xenon near2 difluoride) near3 etch or etching or etchant) near5 sacrificial) and (semiconductor or chip or die or ic)	USPAT	OR	OFF	2004/08/12 15:54
S11	215	(xenon near2 difluoride)	USPAT	OR	OFF	2004/08/12 15:54

S12	28	((xenon near2 difluoride)) and (sacrificial near5 (etch etching or etchant))	USPAT	OR	OFF	2005/08/03 17:40
S13	1	("6015599").PN.	USPAT	OR	OFF	2005/02/18 13:19
S14	1	("6117748").PN.	USPAT	OR	OFF	2005/02/18 13:19
S15	1	("6331459").PN.	USPAT	OR	OFF	2005/02/18 13:19
S16	1	("6372632").PN.	USPAT	OR	OFF	2005/02/18 13:20
S17	1	("6436787").PN.	USPAT	OR	OFF	2005/02/18 13:20
S18	1	("6461888").PN.	USPAT	OR	OFF	2005/02/18 13:20
S19	1	("6496348").PN.	USPAT	OR	OFF	2005/02/18 13:20
S20	1	("6531331").PN.	USPAT	OR	OFF	2005/02/18 13:20
S21	1	("6555467").PN.	USPAT	OR	OFF	2005/02/18 13:20
S22	1	("20030036215").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/18 13:21
S23	1	("20030054588").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/18 13:21
S24	11	S13 S14 S15 S16 S17 S18 S19 S20 S21 S22 S23	US-PGPUB; USPAT	OR	OFF	2005/02/18 13:35
S25	1	("6835616").PN.	USPAT	OR	OFF	2005/02/18 14:20
S26	1	("20020047172").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/18 14:20
S27	170	(via or vias) and ((sacrificial with (etch or etching)) same (air near2 (gap or core or void or slot or space or pocket)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 15:46
S28	1	("6835616").PN.	USPAT	OR	OFF	2005/08/03 15:45
S29	56	S27 and damascene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:03
S30	434	438/244.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:03
S31	0	438/253].ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:03

S32	2404	438/253.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:03
S33	745	438/296.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:03
S34	281	438/387.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:03
S35	525	438/397.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:06
S36	591	438/254.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:06
S38	1252	257/750.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:03
S39	2404	438/253.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:06
S40	4364	438/396.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:06
S41	8092	S30 S32 S33 S34 S35 S36 S37 S38 S39 S40	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:06
S42	5601	S41 and (etching or etch or etchant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:08

S43	1805	S42 and (fluoride or f)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:08
S44	656	S41 and ((etching or etch or etchant) with (fluoride or f))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:09
S45	37	S44 and air	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:11
S46	0	S44 not S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:11
S47	619	S44 not S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:11
S48	162	((xenon near2 difluoride)) and (sacrificial near5 (etch etching or etchant))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:40
S49	161	S48 not S47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:41
S50	160	S49 not S44	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 17:41